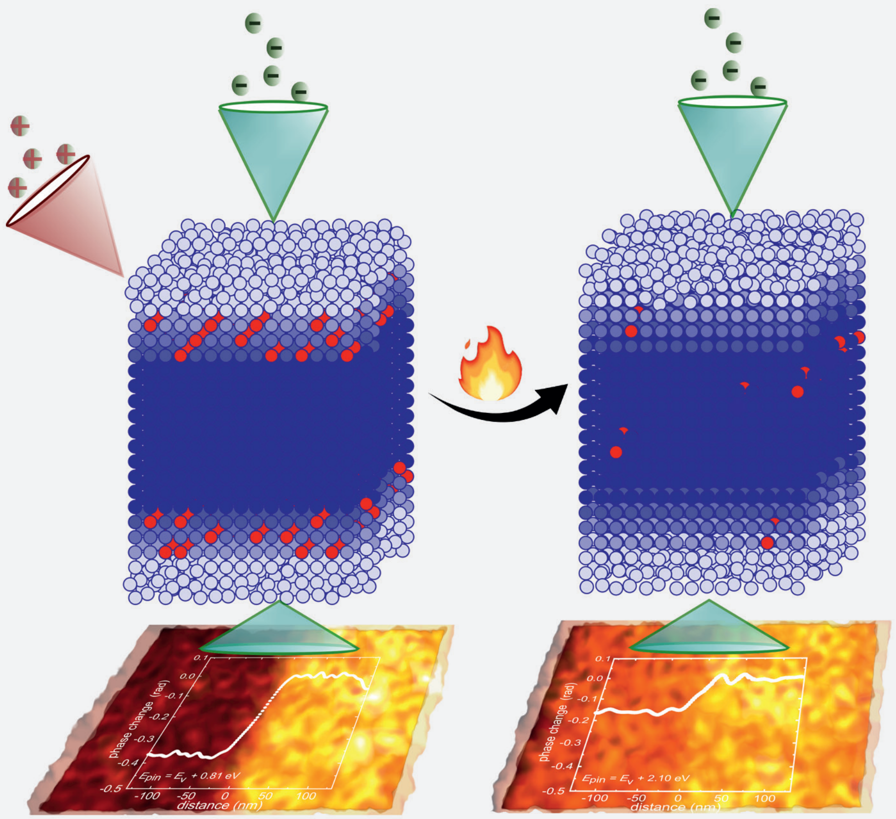

Quantitative investigation of point defects and their dynamics in focused ion beam-prepared group III-nitride lamellas by off-axis electron holography

Keyan Ji

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